

# Ultra High-PSRR, Low-Noise, 300mA CMOS

## **Linear Regulator**

#### **General Description**

The EMP8130 features ultra-high power supply rejection ratio, low output voltage noise, low dropout voltage, low quiescent current and fast transient response. It guarantees delivery of 300mA output current and supports preset output voltages ranging from 0.8V to 4.5V with 0.1V increment.

Based on its low quiescent current consumption and its less than 1uA shutdown mode of logical operation, the EMP8130 is ideal for battery-powered applications. The high power supply rejection ratio of the EMP8130 holds well for low input voltages typically encountered in battery-operated systems. The regulator is stable with small ceramic capacitive loads.

The EMP8130 offers current fold-back which throttles down the output current with a decrease in load resistance. The typical value at which current fold-back kicks in is 420mA; the typical value of the output short current limit value is 40mA.

The EMP8130 is available in miniature SOT-23-5,

#### Typical Application

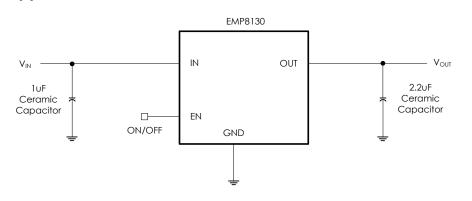
uDFN-4, SOT-23-3 and TDFN-6 package.

#### **Applications**

- Wireless handsets
- PCMCIA cards
- DSP core power
- Hand-held instruments
- Battery-powered systems
- Portable information appliances

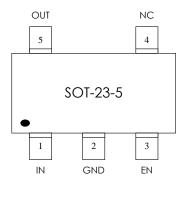
#### **Features**

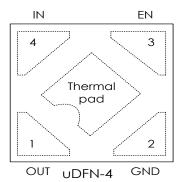
- 300mA guaranteed output current
- 75dB typical PSRR at 1kHz
- 260mV (V<sub>OUT</sub>=3.3V) typical dropout at 300mA
- 52µA typical quiescent current
- Less than 1µA typical shutdown mode
- Fast line and load transient response
- 1.7V to 5.5V input range
- Auto-discharge during chip disable
- 0.8V to 4.5V output voltage range
- Stable with small ceramic output capacitors
- Fold-back over current protection
- ±1% output voltage tolerance

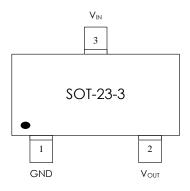


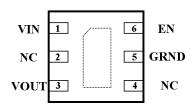


### **Connection Diagrams**









## Order information

XX	Output voltage
VN05	SOT-23-5 Package
NRR	RoHS & Halogen free package Rating: -40 to 85°C Package in Tape & Reel

#### EMP8130-XXFJ04NRR

XX	Output voltage
FJ04	uDFN-4 Package
NRR	RoHS & Halogen free package Rating: -40 to 85°C Package in Tape & Reel

EMP8130	D-XXVN03NRR
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XX	Output voltage
VN03	SOT-23-3 Package
NRR	RoHS & Halogen free package Rating: -40 to 85°C Package in Tape & Reel

#### EMP8130-XXFK06NRR

XX	Output voltage
FK06	TDFN-6 Package
NRR	RoHS & Halogen free package Rating: -40 to 85°C Package in Tape & Reel

Order,	Marking	&	Packing	Information
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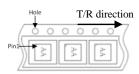
Package	Vout	Product ID.	Marking	Packing
	0.8V	EMP8130-08VN05NRR (By request)		
	1.0V	EMP8130-10VN05NRR		
	1.1V	EMP8130-11VN05NRR		
	1.2V	EMP8130-12VN05NRR		
	1.3V	EMP8130-13VN05NRR (By request)	5 4	Tape & Reel 3Kpcs
SOT-23-5	1.5V	EMP8130-15VN05NRR	8130	
301-23-3	1.8V	EMP8130-18VN05NRR	Tracking Code	
	2.5∨	EMP8130-25VN05NRR		
	2.7V	EMP8130-27VN05NRR (By request)		
	2.8V	EMP8130-28VN05NRR	]	
	3.0V	EMP8130-30VN05NRR	]	
	3.3∨	EMP8130-33VN05NRR		

Package	Vout	Product ID.	Marking	Packing
	0.8V	EMP8130-08FJ04NRR (By request)	Pin1 $\longrightarrow$ X X = tracking code	
	1.0V	EMP8130-10FJ04NRR (By request)	Pin1 $\longrightarrow$ $\overline{X} \ \overline{X}$ X X = tracking code	
uDFN-4	1.1V	EMP8130-11FJ04NRR (By request)	Pin1 $\longrightarrow$ X X X X = tracking code	Tape & Reel 8Kpcs
	1.2V	EMP8130-12FJ04NRR	Pin1 $\longrightarrow$ $\overline{X}  \overline{X}$ X X = tracking code	
	1.3V	EMP8130-13FJ04NRR (By request)	Pin1 $\longrightarrow$ $X X = \text{tracking code}$	



# EMP8130

1.5V	EMP8130-15FJ04NRR (By request)	Pin1 $\longrightarrow$ X X X = tracking code	
1.8V	EMP8130-18FJ04NRR	Pin1 $\longrightarrow$ $X X$ X X = tracking code	
2.5V	EMP8130-25FJ04NRR	Pin1 $\longrightarrow$ $\overline{X} \ \overline{X}$ X X = tracking code	
2.8V	EMP8130-28FJ04NRR	Pin1 $\longrightarrow$ X $\overline{X}$ X X = tracking code	
3.0V	EMP8130-30FJ04NRR	Pin1 $\longrightarrow$ $\overline{X} \ X$ X X = tracking code	
3.3V	EMP8130-33FJ04NRR	Pin1 $\longrightarrow$ X X X X = tracking code	



Note: When the hole is located above the tape, the pin1 of the IC is located on the upper left.

Package	Vout	Product ID.	Marking	Packing
	1.2V	EMP8130-12VN03NRR (By request)		de Tape & Reel 3Kpcs
	1.5V	EMP8130-15VN03NRR		
	1.8V	EMP8130-18VN03NRR	3	
501.02.2	2.5V	EMP8130-25VN03NRR (By request)	8130	
SOT-23-3 -	2.8V	EMP8130-28VN03NRR	PIN1 DOT	
	3.0V	EMP8130-30VN03NRR		
	3.3∨	EMP8130-33VN03NRR		
	4.2V	EMP8130-42VN03NRR (By request)		



# EMP8130

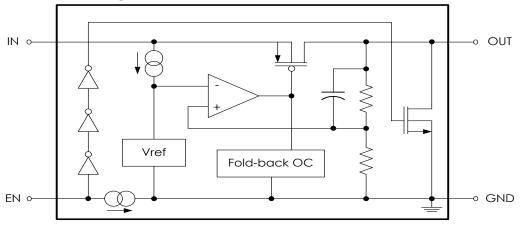
Package	Vout	Product ID.	Marking	Packing
	1.2V	EMP8130-12FK06NRR (By request)	6 5 4	Tape & Reel 3Kpcs
	1.8V	EMP8130-18FK06NRR (By request)	8130 Tracking Code	
TDFN-6	2.8V	EMP8130-28FK06NRR (By request)		
	3.0V	EMP8130-30FK06NRR (By request)		
	3.3V	EMP8130-33FK06NRR (By request)	PINI DOT	



### **Pin Functions**

Name	SOT-23-5	uDFN-4	SOT-23-3	TDFN-6	Function				
IN	1	4	3	1	Supply Voltage Input. Require a minimum input capacitor of close to 1µF cerar capacitor to ensure stability and sufficient decoupling from ground pin.				
GND	2	2	1	5	Ground Pin.				
EN	3	3	N/A	6	<b>Enable Input.</b> Enable the regulator by pulling the EN pin High. To keep the regulator on during normal operation, connect the EN pin to $V_{IN}$ . The EN pin must not exceed $V_{IN}$ under all operating conditions.				
NC	4	N/A	N/A	2,4	No Connected.				
Ουτ	5	1	2	3	<b>Regulated Output Voltage Pin.</b> A small 2.2µF ceramic capacitor is needed from this pin to ground to assure stability.				
Thermal Pad	N/A	YES	N/A	YES	The thermal pad with large thermal land area on the PCB v helpful chip power dissipation, to connect it to GND togeth normally.				

## Functional Block Diagram





#### Absolute Maximum Ratings (Notes 1, 2)

-	
IN, EN, OUT	-0.3V to 6.5V
Power Dissipation	(Note 6)
Storage Temperature Range	-65°C to 150°C
Junction Temperature (T <sub>J</sub> )	150°C

Lead Temperature (Soldering, 10 sec.)	260°C
ESD Rating	
Human Body Model	2KV
Machine Model	200V

#### **Operating Ratings** (Note 1, 2)

1.7V to 5.5V

Operating Temperature Range -40°C to 85°C

#### **Thermal Resistance:**

Supply Voltage

Symbol	<b>0JA</b> (Note 3)	<b>ØJc</b> (Note 4)
SOT-23-5	152(°C/W)	81(°C/W)
uDFN-4	110(°C/W)	23(°C/W)
SOT-23-3	250(°C/W)	81(°C/W)
TDFN-6	165(°C/W)	20(°C/W)

#### **Electrical Characteristics**

Unless otherwise specified, all limits guaranteed for  $V_{IN} = V_{OUT} + 1V$  (Note 5),  $V_{EN} = V_{IN}$ ,  $C_{IN} = 1\mu$ F,  $C_{OUT} = 2.2\nu$ F,  $T_A = 25^{\circ}$ C. **Boldface** limits apply for the operating temperature extremes: -40°C and 85°C.

Symbol	Parameter	Conditions	Min	<b>Typ</b> (Note 7)	Max	Units		
V <sub>IN</sub>	Input Voltage		1.7		5.5	V		
Vout	Output Voltage		0.8		4.5	V		
		Vout>2.0V, T=25	X0.99		X1.01	V		
A \/	Output Valtage Telerance	Vout<=2.0V, T=25	-20		+20	mV		
$\Delta V_{OTL}$	Output Voltage Tolerance	Vout>2V, -40~85C	X0.97		X1.03	V		
		Vout<=2V, -40~85C	-60		60	mV		
IOUT	Maximum Output Current	Average DC Current Rating	300			mA		
Ici	Current Limit	Vin=Vout+1V		420		mA		
lsc	Short Current Limit			40		mA		
lq	Quiescent Current	Iout = 0mA		52	75	μA		
Isd	Shutdown Supply Current	V <sub>OUT</sub> = 0V, EN = GND		0.2	1	μA		
		I <sub>OUT</sub> = 300mA, Vout=0.8V		860				
		I <sub>ουτ</sub> = 300mA, Vout=1.1V		650				
		I <sub>ουτ</sub> = 300mA, Vout=1.2V		580				
V <sub>DO</sub>	Dropout Voltage (Note 5)	I <sub>ουτ</sub> = 300mA, Vout=1.5V		440		mV		
		I <sub>OUT</sub> = 300mA, Vout=1.8V		380				
		I <sub>OUT</sub> = 300mA, Vout=2.8V		290				
		I <sub>OUT</sub> = 300mA, Vout=3.3V		260				
	Line Regulation	$I_{OUT} = 1 \text{mA}, (V_{OUT} + 1 \text{V}) \le V_{IN} \le 5.5 \text{V}$		0.02	0.1	%/V		
Δ VOUT	Load Regulation	1mA ≤ I <sub>OUT</sub> ≤ 300mA		10	30	mV		
PSRR	Power supply rejection ratio	f = 1kHz, Ripple 0.2 Vp-p,		75		dB		
FJKK		Vin=Set Vout +1V, lout = 30mA		75		ЧЪ		
en	Output Voltage Noise	V <sub>OUT</sub> =0.8V, I <sub>OUT</sub> =30mA, 10Hz ≤ f ≤ 100kHz		40		μV <sub>RMS</sub>		
V <sub>EN</sub>	EN Input Threshold		1.0			V		



					0.4	
IE	ĪN	EN Input Bias Current	EN=GND or VIN	0.1	1	μA

**Note 1:** Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.

Note 2: All voltages are with respect to the potential at the ground pin.

Note 3:  $\theta_{JA}$  is measured in the natural convection at  $T_A=25^{\circ}C$  on a high effective thermal conductivity test board (2 layers, 2SOP).

Note 4:  $\theta_{JC}$  represents the resistance to the heat flows the chip to package top case.

**Note 5:** Dropout voltage is measured by reducing  $V_{IN}$  until  $V_{OUT}$  drops 100mV from its nominal value at  $V_{IN} - V_{OUT} = 1V$ .

**Note 6:** Maximum Power dissipation for the device is calculated using the following equations:

$$P_{D} = \frac{T_{J(MAX)} - T_{A}}{\theta_{JA}}$$

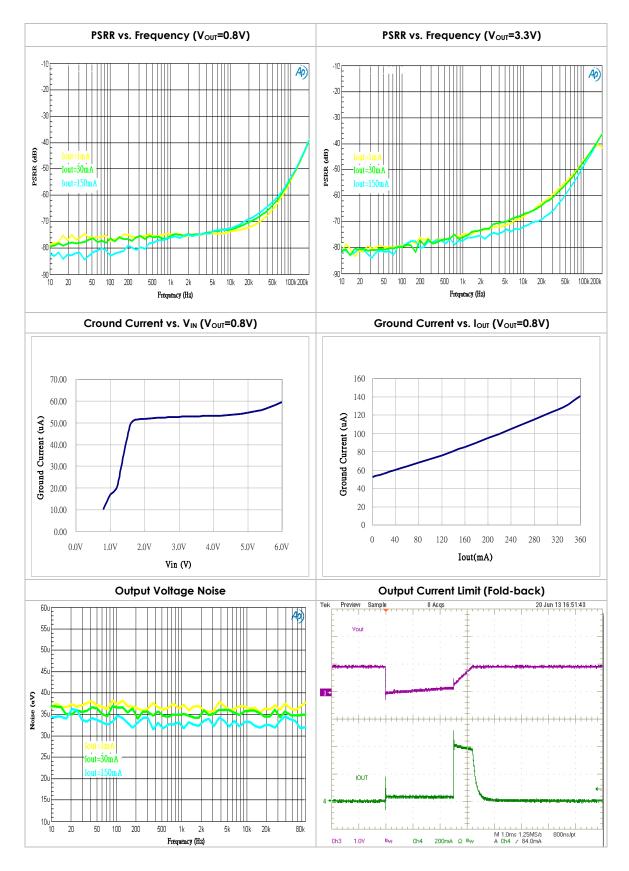
Where  $T_J(MAX)$  is the maximum junction temperature,  $T_A$  is the ambient temperature, and  $\theta_{JA}$  is the junction-to-ambient thermal resistance. E.g. for the SOT-23-5 package $\theta_{JA} = 152^{\circ}C/W$ ,  $T_J(MAX) = 150^{\circ}C$  and using  $T_A = 25^{\circ}C$ , the maximum power dissipation is found to be 0.82W. The derating factor (-1/ $\theta_{JA}$ ) = -6.6mW/°C, thus below 25°C the power dissipation figure can be increased by 6.6mW per degree, and similarity decreased by this factor for temperatures above 25°C.

Note 7: Typical values represent the most likely parametric norm.



## **Typical Performance Characteristics**

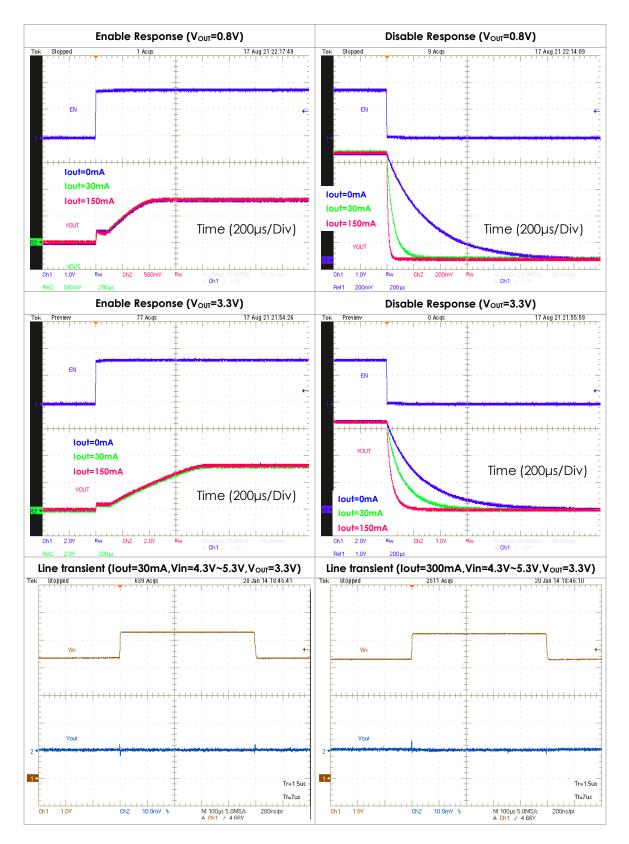
Unless otherwise specified,  $V_{IN} = V_{OUT (NOM)} + 1V$ ,  $V_{EN} = V_{IN}$ ,  $C_{IN} = 1\mu$ F,  $C_{OUT} = 2.2\nu$ F,  $T_A = 25^{\circ}$ C





## Typical Performance Characteristics (cont.)

Unless otherwise specified,  $V_{IN} = V_{OUT (NOM)} + 1V$ ,  $V_{EN} = V_{IN}$ ,  $C_{IN} = 1\mu$ F,  $C_{OUT} = 2.2\mu$ F,  $T_A = 25^{\circ}$ C





## Typical Performance Characteristics (cont.)

Unless otherwise specified,  $V_{IN} = V_{OUT (NOM)} + 1V$ ,  $V_{EN} = V_{IN}$ ,  $C_{IN} = 1\mu$ F,  $C_{OUT} = 2.2\nu$ F,  $T_A = 25^{\circ}$ C

	Load transient (Vout=0.8V, lout=50mA to 100mA)							Load transient (Vour=0.8V, Iour=1mA to 300mA)						<b>A)</b>						
⊧k	Stopped		73	Acqs			17 .	an 14 16:3	39:54	Tek		ed		42	Acqs			17 J	an 14 16:8	51:49
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ŧ	1	1	1		‡	-		1	Tf=260ns			1		1		‡	1	-		Tf=250
L			Ch2	20.0mV %	Bw	M 40.0µs	2.565/s	400ps/	trinit			1		Ch2	100mV %	Bw	M 40.0µs	2.5GS/s	400ps/	 at
			Ch4	50.0mA Ω		A Ch4 /	65.0mA								100mA Ω	BW	A Ch4 /		also if	

## **Application Information**

#### **General Description**

Referring to Fig.1 as shown in the Functional Block Diagram section, the EMP8130 adopts the classical regulator topology in which negative feedback control is used to perform the desired voltage regulating function. The sub Vout-select form the feedback circuit which samples the output voltage for the error amplifier's non-inverting input. The inverting input is set to the bandgap reference voltage. Due to its high open-loop gain, the error amplifier ensures that the sampled output feedback voltage at its non-inverting input is virtually equal to the preset voltage reference voltage. The error amplifier compares the voltage difference at its inputs and produces an appropriate driving voltage to the P-channel MOS pass transistor, which controls the amount of current reaching the output. If there are changes in the output voltage due to load changes, the feedback resistors register these changes to the non-inverting input of the error amplifier. The error amplifier then adjusts its driving voltage to maintain virtual short between its two input nodes under all loading conditions. The regulation of the output voltage is achieved as a direct result of the error amplifier keeping its input voltages equal. This negative feedback control topology is further augmented by the shutdown, the temperature and current protection circuitry.

#### **Output Capacitor**

The EMP8130 is specially designed for use with ceramic output capacitors of as low as 2.2 $\mu$ F to take advantage of the savings in cost and space, as well as the superior filtering of high frequency noise. Capacitors of higher value or other types may be used, but it is important to make sure its equivalent series resistance (ESR) be restricted to less than 0.5 $\Omega$ . The use of larger capacitors with smaller ESR values is desirable for applications involving large and fast input or output transients, as well as situations where the application systems are not physically located immediately adjacent to the battery power source. Typical ceramic capacitors suitable for use with the EMP8130 are X5R and X7R. The X5R and the X7R capacitors are able to maintain their capacitance values to within ±20% and ±10%, respectively, as the temperature increases.

#### **No-Load Stability**

The EMP8130 is capable of stable operation during no-load conditions, a mandatory feature for some applications such as CMOS RAM keep-alive operations.

#### Input Capacitor

A minimum input capacitance of 1µF is required for EMP8130. The capacitor value may be increased without limit. Improper workbench set-ups may have adverse effects on the normal operation of the regulator. A case in point is the instability that may result from long supply lead inductance coupling to the output through the gate capacitance of the pass transistor. This will establish a pseudo LCR network, and is likely to happen under high current conditions or near dropout. A 10µF tantalum input capacitor will dampen the parasitic LCR action thanks to its high ESR. However, cautions should be exercised to avoid regulator short-circuit damage when tantalum capacitors are used, for they are prone to fail in short-circuit operating conditions.



#### **Power Dissipation**

Thermal overload results from excessive power dissipation that causes the IC junction temperature to increase beyond a safe operating level. The concept of thermal resistance  $\theta_{JA}$  (°C/W) is often used to describe an IC junction's relative readiness in allowing its thermal energy to dissipate to its ambient air. An IC junction with a low thermal resistance is preferred because it is relatively effective in dissipating its thermal energy to its ambient, thus resulting in a relatively low and desirable junction temperature. The relationship between  $\theta_{JA}$  and T<sub>J</sub> is as follows:

 $T_{J} = \Theta_{JA} \times (P_{D}) + T_{A}$ 

 $T_{\text{A}}$  is the ambient temperature, and  $P_{\text{D}}$  is the power generated by the IC and can be written as:

 $P_D = I_{OUT} (V_{IN} - V_{OUT})$ 

As the above equations show, it is desirable to work with Ics whose  $\theta_{JA}$  values are small such that  $T_J$  does not increase strongly with P<sub>D</sub>. To avoid thermally overloading the EMP8130, refrain from exceeding the absolute maximum junction temperature rating of 150°C under continuous operating conditions. Overstressing the regulator with high loading currents and elevated input-to-output differential voltages can increase the IC die temperature significantly.

#### Shutdown

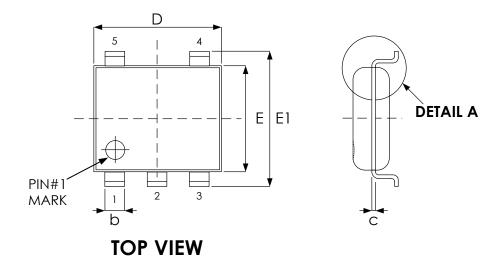
The EMP8130 enters sleep mode when the EN pin is low. When this occurs, the pass transistor, the error amplifier, and the biasing circuits, including the bandgap reference, are turned off, thus reducing the supply current to typically < 1uA. The low supply current makes the EMP8130 best suited for battery-powered applications. The maximum guaranteed voltage at the EN pin to enter sleep mode is 0.4V. A minimum guaranteed voltage of 1.0V at the EN pin will activate the EMP8130. To constantly keep the regulator on, direct connection of the EN pin to the VIN pin is allowed.

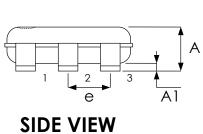
#### Fold-back Over Current Protection

The EMP8130 has an internal fold-back current limit that helps to protect the regulator during fault conditions. The current supplied by the device is gradually throttled down as the output voltage decreases. When the output is shorted, the LDO supplies a typical current of 40mA. Output voltage is not regulated when the device is in current limit, VOUT=ILIMIT x RLOAD. The advantage of fold-back current limit is that the ILIMIT value is less than the fixed current limit. Therefore, the power that the PMOS pass transistor dissipates is much less.



Package Outline Drawing SOT-23-5



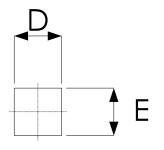


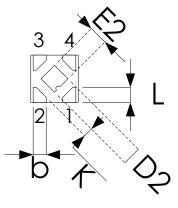
DETAIL A

Court of	Dimension in mm					
Symbol	Min.	Max.				
А	0.90	1.45				
A1	0.00	0.15				
b	0.30	0.50				
С	0.08	0.25				
D	2.70	3.10				
Е	1.40	1.80				
E1	2.60	3.00				
е	0.95	BSC				
L	0.30	0.60				



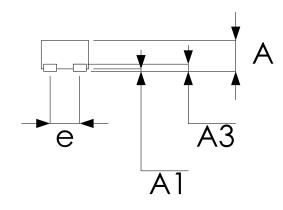
Package Outline Drawing uDFN-4L (1mmx1 mm)





## **TOP VIEW**

**BOTTOM VIEW** 



## **SIDE VIEW**

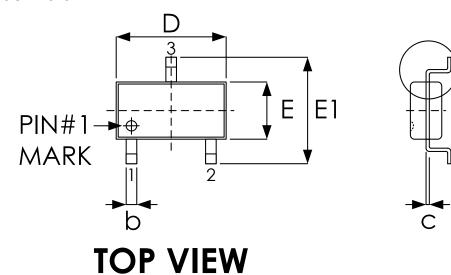
Symbol	Dimension in mm				
Symbol	Min	Max			
А	0.35	0.60			
A1	0.00	0.05			
A3	0.12 REF.				
b	0.175	0.275			
D	1.00 BSC				
Е	1.00 BSC				
е	0.625 BSC				
L	0.200	0.300			
K	0.20	-			

Exposed pad
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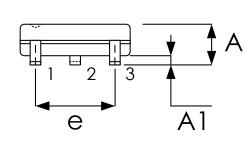
	Dimensio	on in mm		
	Min	Max		
D2	0.40	0.60		
E2	0.40	0.60		



Package Outline Drawing SOT-23-3



DETAIL A



**SIDE VIEW** 

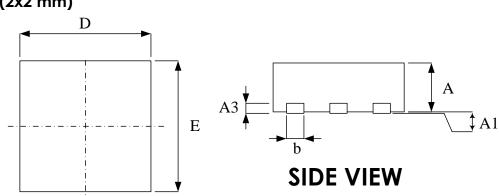
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**DETAIL A** 

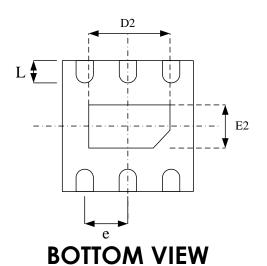
Symbol	Dimension in mm	
	Min.	Max.
А	0.90	1.45
A1	0.00	0.15
b	0.30	0.50
С	0.08	0.25
D	2.70	3.10
Е	1.40	1.80
E1	2.60	3.00
е	1.90	BSC
L	0.30	0.60



Package Outline Drawing TDFN-6L (2x2 mm)



# **TOP VIEW**



Sumbol	Dimension in mm	
Symbol	Min	Max
А	0.70	0.80
A1	0.00	0.05
A3	0.18	0.25
b	0.25	0.35
D	1.90	2.10
Е	1.90	2.10
е	0.65	BSC
L	0.20	0.45

Exposed	pad	option
LAPOSCU	pau	option

	Dimension in mm	
	Min	Max
D2	1.35	1.45
E2	0.55	0.65



## **Revision History**

Revision	Date	Description
0.1	2014.02.11	Initial version.
0.2	2014.05.12	Add uDFN package information
0.3	2014.06.13	Add electrical Characteristics for Icl
0.4	2014.08.22	Add uDFN Thermal Resistance
0.5	2015.01.16	<ol> <li>Add uDFN PIN number</li> <li>Electrical characteristics format corrected.</li> <li>Add package information SC70 and SC82.</li> </ol>
1.0	2015.03.11	Revise version to 1.0 & remove preliminary word
1.1	2015.05.27	Modify connection diagrams and pin functions for uDFN-4
1.2	2015.10.07	Modify application for Output Capacitor(2.2uF)
1.3	2015.11.02	Add TSOT23-5 package information
1.4	2015.11.09	Cancel pin1 dot for uDFN-4 marking
1.5	2016.12.14	Add SOT23-3/TDFN-6 package information
1.6	2017.04.26	Add 2.7V voltage option for SOT23-5 package
1.7	2017.07.31	Add 1.5V/2.5V voltage option for SOT23-3 package
1.8	2017.09.15	Add 1.1V voltage option for SOT23-5 package
1.9	2017.11.14	Add application Information for fold-back current protection
2.0	2017.12.21	1.Update Vout range to 4.5V from 4.0V 2. Add 4.2V voltage option for SOT23-3 package
2.1	2018.01.30	<ol> <li>Add 1.1V voltage option for uDFN-4 package</li> <li>Add dropout voltage for 1.1V</li> <li>Update uDFN-4 POD</li> </ol>
2.2	2020.07.03	1.Remove old order, Marking & Packing Information 2.Add Pin1 location description for UDFN 3.Modify FJ04 package image of Connection Diagrams
2.3	2020.11.19	1.Remove SC70-5,SC82-4 and TSO23-5 package option 2.Add by request for product id
2.4	2021.08.27	Update enable and disable response plots
2.5	2021.09.14	For customer request modify enable and disable response plots.



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